PBHV8115T

150 V, 1 A NPN high-voltage low VCEsat transistor

Product data sheet

1. General description

NPN high-voltage low V_{CEsat} transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9115T

2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- Small SMD plastic package

3. Applications

- LED driver for LED chain module
- LCD backlighting
- · High Intensity Discharge (HID) front lighting
- Automotive motor management
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	150	V
I _C	collector current		-	-	1	Α
h _{FE}	DC current gain	$V_{CE} = 10 \text{ V}; I_{C} = 50 \text{ mA}; T_{amb} = 25 \text{ °C}$	100	250	-	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	Е	emitter		j
3	С	collector		В — 🛴
				 E
			1	sym021
			SOT23	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBHV8115T	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBHV8115T	W6%

[1] % = placeholder for manufacturing site code

1 January 2023

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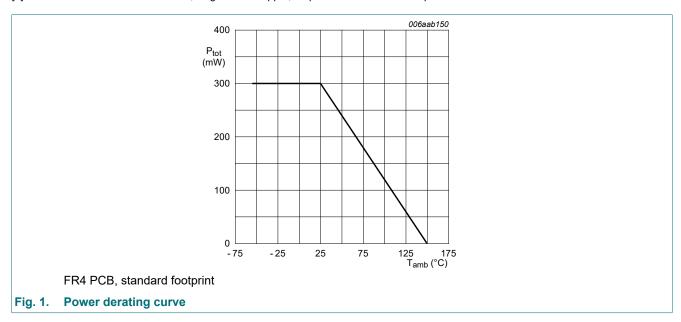
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	400	V
V _{CEO}	collector-emitter voltage	open base		-	150	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
Ic	collector current			-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	2	Α
I _{BM}	peak base current			-	400	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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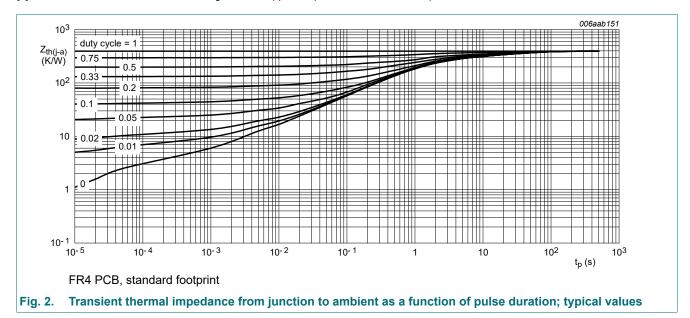
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	70	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



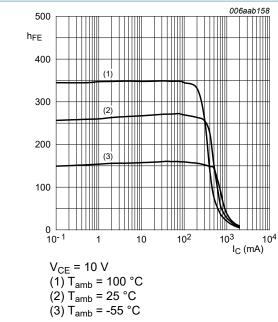
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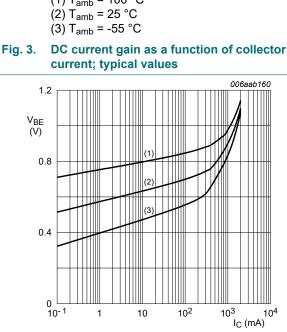
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 120 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 120 V; I _E = 0 A; T _j = 150 °C	-	-	10	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = 120 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 50 mA; T _{amb} = 25 °C	100	250	-	
		V _{CE} = 10 V; I _C = 100 mA; T _{amb} = 25 °C	100	250	-	
		V_{CE} = 10 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	50	160	-	
		V_{CE} = 10 V; I_{C} = 1 A; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	10	30	-	
OLOGI	collector-emitter	I _C = 100 mA; I _B = 10 mA; T _{amb} = 25 °C	-	40	60	mV
	saturation voltage	I _C = 100 mA; I _B = 20 mA; T _{amb} = 25 °C	-	33	50	mV
		I_C = 1 A; I_B = 200 mA; pulsed; $t_p \le$	-	225	350	mV
V _{BEsat}	base-emitter saturation voltage	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	1.1	1.2	V
t _d	delay time	V _{CC} = 6 V; I _C = 0.5 A; I _{Bon} = 0.1 A;	-	7	-	ns
t _r	rise time	I _{Boff} = -0.1 A; T _{amb} = 25 °C	-	565	-	ns
t _{on}	turn-on time		-	572	-	ns
t _s	storage time		-	1530	-	ns
t _f	fall time		-	700	-	ns
t _{off}	turn-off time		-	2230	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	-	30	-	MHz
C _c	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	5.7	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	150	-	pF

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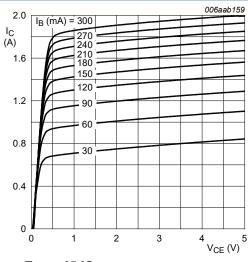




(1) T_{amb} = -55 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

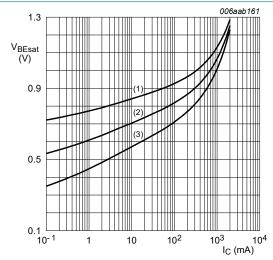
 V_{CE} = 10 V

Fig. 5. Base-emitter voltage as a function of collector current; typical values



T_{amb} = 25 °C

Fig. 4. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 5$

 $(1) T_{amb} = -55 °C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values

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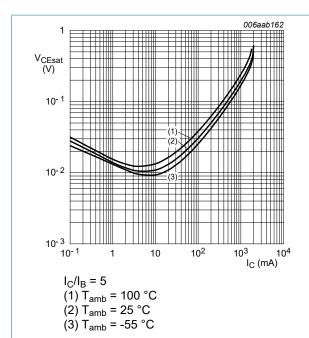


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

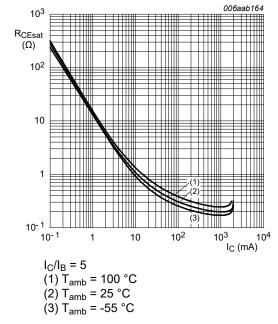


Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values

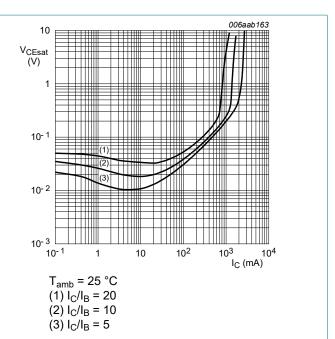


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

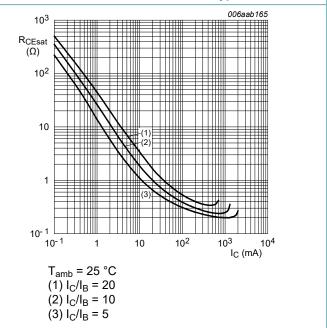
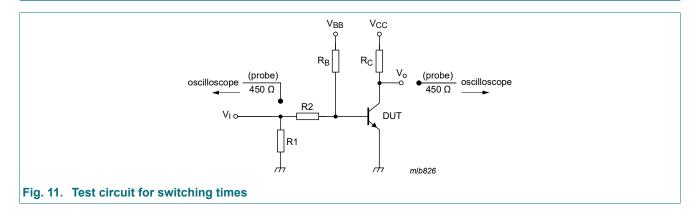


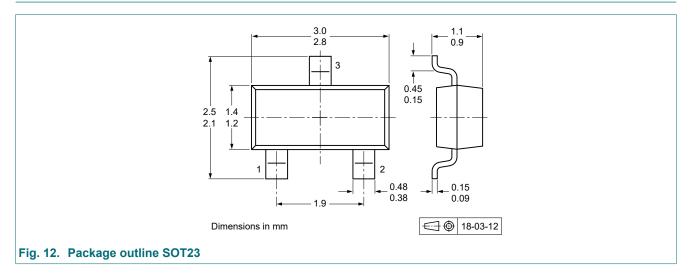
Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

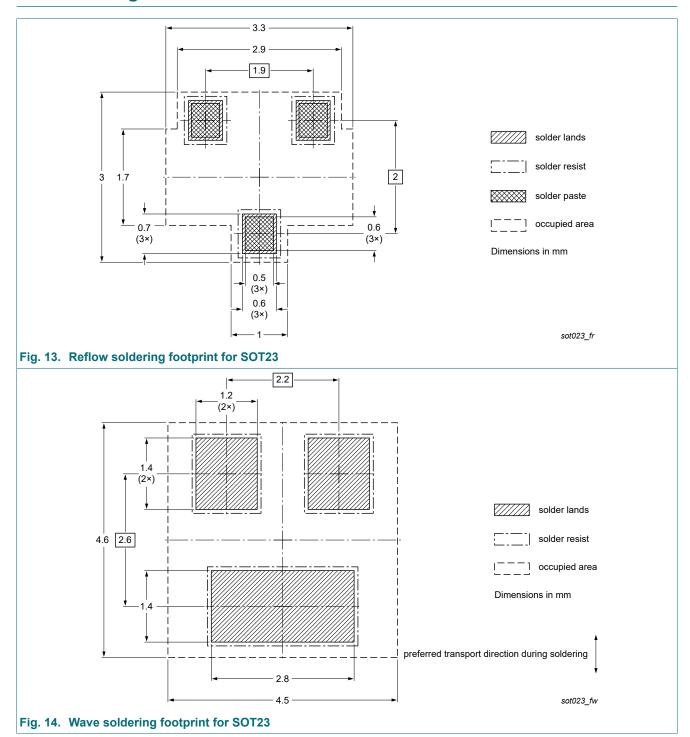


12. Package outline



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13. Soldering



Product data sheet

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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8115T v.3	20230101	Product data sheet	-	PBHV8115T_2
Modifications:	Nexperia. • Legal texts hav	ernative(s).	company name where	
PBHV8115T_2	20081209	Product data sheet	-	PBHV8115T_1
PBHV8115T_1	20080204	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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